1 GHz, 25 dB gain GaAs high output power doublerRev. 1 — 5 April 2011Product

Product data sheet

Product profile 1.

1.1 General description

Hybrid amplifier module in a SOT115J package, operating at a supply voltage of 24 V Direct Current (DC), employing Hetero junction Field Effect Transistor (HFET) GaAs dies.

1.2 Features and benefits

- Excellent linearity
- Optimized for flat PAL D and flat NTSC loading
- Superior levels of ESD protection
- Extremely low noise
- Excellent return loss properties
- Gain compensation over temperature
- Rugged construction
- Unconditionally stable
- Thermally optimized design
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)
- Integrated ring wave surge protection

1.3 Applications

CATV systems operating in the 40 MHz to 862 MHz / 1003 MHz frequency range using PAL D or NTSC channel conditions.

1.4 Quick reference data

Quick reference data Table 1.

Bandwidth 40 MHz to 1003 MHz; $V_B = 24 V (DC)$; $Z_S = Z_L = 75 \Omega$; $T_{mb} = 35$ °C; unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Gp	power gain	f = 50 MHz		-	23.2	-	dB
		f = 1003 MHz		23.5	24.4	25.5	dB
СТВ	composite triple beat	$V_o = 48 \text{ dBmV}$ at 862 MHz	[1]	-	-66	-62	dBc
CSO	composite second-order distortion	$V_o = 48 \text{ dBmV}$ at 862 MHz	[1]	-	-69	-62	dBc
I _{tot}	total current		[2]	-	440	460	mA

[1] 98 PAL D channels with 8 MHz bandwidth per channel; [f = 47 MHz to 862 MHz]; flat V_0 till 862 MHz.

[2] Direct Current (DC).



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2. Pinning information

Table 2.	Pinning	
Pin	Description	Simplified outline Graphic symbol
1	input	
2, 3	common	1 3 5 7 9
5	+V _B	
7, 8	common	
9	output	2 3 7 8 sym095

3. Ordering information

Table 3. Ordering information						
Type number	Раскае	Package				
	Name	Description	Version			
CGD985HCI	-	rectangular single-ended package; aluminium flange; 2 vertical mounting holes; $2 \times 6-32$ UNC and 2 extra horizontal mounting holes; 7 gold-plated in-line leads	SOT115J			

4. Limiting values

Table 4.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
VB	supply voltage		-	30	V
V _{i(RF)}	RF input voltage	single tone	-	75	dBmV
V _{ESD}	electrostatic discharge voltage	Human Body Model (HBM); According JEDEC standard 22-A114E	<u>[1]</u> -	2000	V
		Biased; According IEC61000-4-2	-	1500	V
T _{stg}	storage temperature		-40	+100	°C
T _{mb}	mounting base temperature		-20	+100	°C

[1] The ESD pulse of 2000 V corresponds to a class 2 sensitivity level.

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5. Characteristics

Table 5. Characteristics

Bandwidth 40 MHz to 1003 MHz; $V_B = 24 V (DC)$; $Z_S = Z_L = 75 \Omega$; $T_{mb} = 35 °C$; unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
G _p	power gain	f = 50 MHz		-	23.2	-	dB
		f = 870 MHz		-	24.0	-	dB
		f = 1003 MHz		23.5	24.4	25.5	dB
SL _{sl}	slope straight line	f = 40 MHz to 1003 MHz	[1]	0.5	-	2	dB
FL	flatness of frequency response	f = 40 MHz to 1003 MHz	[2]	-	-	1	dB
RL _{in}	input return loss	f = 40 MHz to 160 MHz		20	-	-	dB
		f = 160 MHz to 320 MHz		20	-	-	dB
		f = 320 MHz to 640 MHz		19	-	-	dB
		f = 640 MHz to 870 MHz		17	-	-	dB
		f = 870 MHz to 1003 MHz		16	-	-	dB
RL _{out}	output return loss	f = 40 MHz to 160 MHz		20	-	-	dB
		f = 160 MHz to 320 MHz		20	-	-	dB
		f = 320 MHz to 640 MHz		19	-	-	dB
		f = 640 MHz to 870 MHz		18	-	-	dB
		f = 870 MHz to 1003 MHz		17	-	-	dB
NF	noise figure	f = 50 MHz		-	4.5	5.5	dB
		f = 1003 MHz		-	5	6	dB
I _{tot}	total current		[3]	-	440	460	mA

[1] G_p at 1003 MHz minus G_p at 40 MHz.

[2] Flatness is defined as peak deviation to straight line.

[3] Direct Current (DC).

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
98 PAL C) channels					
СТВ	composite triple beat	$V_o = 48 \text{ dBmV}$ at 862 MHz	<u>[1]</u> -	-66	-62	dBc
		$V_o = 50 \text{ dBmV}$ at 862 MHz	<u>[1]</u> _	-62	-	dBc
CSO	composite second-order distortion	$V_o = 48 \text{ dBmV}$ at 862 MHz	<u>[1]</u> _	-69	-62	dBc
		$V_o = 50 \text{ dBmV}$ at 862 MHz	<u>[1]</u> _	-65	-	dBc
Xmod	cross modulation	$V_o = 48 \text{ dBmV}$ at 862 MHz	<u>[1]</u> _	-68	-	dB
		$V_o = 50 \text{ dBmV}$ at 862 MHz	<u>[1]</u> _	-60	-	dB
112 NTS	C channels					
СТВ	composite triple beat	$V_o = 48 \text{ dBmV}$ at 750 MHz	[2] _	-63	-	dBc
CSO	composite second-order distortion	$V_o = 48 \text{ dBmV}$ at 750 MHz	[2] _	-66	-	dBc
Xmod	cross modulation	$V_o = 48 \text{ dBmV}$ at 750 MHz	[2]	-66	-	dB
79 NTSC	channels + 75 digital channels					
СТВ	composite triple beat	$V_o = 56.4 \text{ dBmV}$ at 1003 MHz	[3]	-75	-	dBc
CSO	composite second-order distortion	$V_o = 56.4 \text{ dBmV}$ at 1003 MHz	[3]	-77	-	dBc
Xmod	cross modulation	$V_o = 56.4 \text{ dBmV}$ at 1003 MHz	<u>[3]</u>	-68	-	dB
CCN	carrier-to-composite noise	V _o = 56.4 dBmV at 1003 MHz	<u>[3]</u> _	57	-	dBc

Table 6. Distortion characteristics

Bandwidth 40 MHz to 1003 MHz; $V_B = 24 V (DC)$; $Z_S = Z_L = 75 \Omega$; $T_{mb} = 35 °C$; unless otherwise specified.

[1] 98 PAL D channels with 8 MHz bandwidth per channel; [f = 47 MHz to 862 MHz]; flat V_o till 862 MHz.

[2] 112 NTSC channels; [f = 45 MHz to 750 MHz]; flat V_0 till 750 MHz.

[3] 79 NTSC channels [f = 54 MHz to 550 MHz] + 75 digital channels [f = 550 MHz to 1003 MHz] (-6 dB offset); tilt extrapolated to 13.5 dB at 1003 MHz.

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CGD985HCI

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6. Package outline

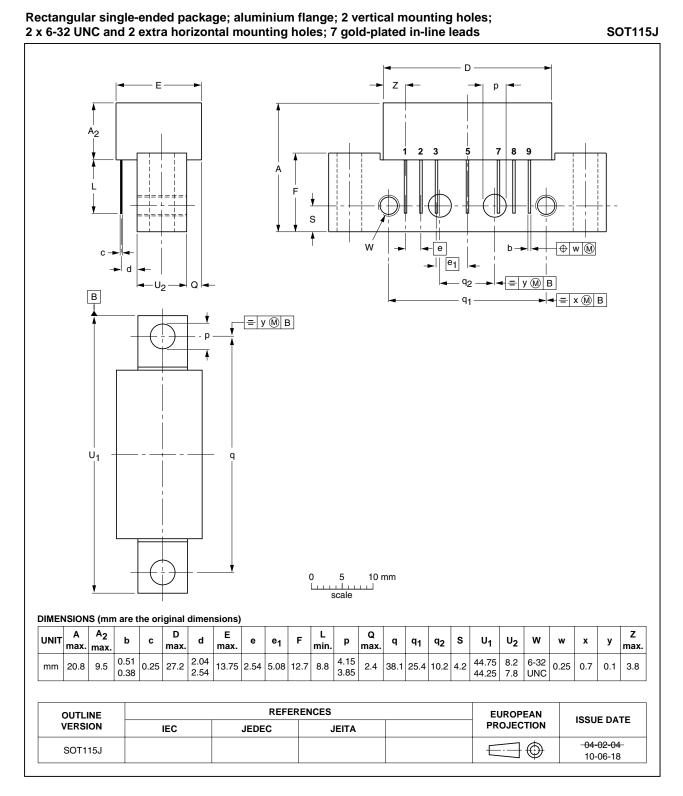


Fig 1. Package outline SOT115J

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7. Abbreviations

Table 7.	Abbreviations
Acronym	Description
CATV	Community Antenna TeleVision
ESD	ElectroStatic Discharge
GaAs	Gallium-Arsenide
NTSC	National Television Standard Committee
PAL	Phase Alternate Line
RF	Radio Frequency
UNC	UNified Coarse
-	

8. Revision history

Table 8. Revis	Revision history					
Document ID	Release date	Data sheet status	Change notice	Supersedes		
CGD985HCI v.1	20110405	Product data sheet	-	-		

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9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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